

# 单 N 沟道 MOSFET

ELM54116WSA-N

<http://www.elm-tech.com>

## ■概要

ELM54116WSA-N 是 N 沟道低输入电容，低工作电压，低导通电阻的大电流 MOSFET。

## ■特点

- $V_{ds}=20V$
- $I_d=15A$
- $R_{ds(on)} = 8.5m\Omega$  ( $V_{gs}=4.5V$ )
- $R_{ds(on)} = 11.0m\Omega$  ( $V_{gs}=2.5V$ )

## ■绝对最大额定值

如没有特别注明时,  $T_a=25^\circ C$

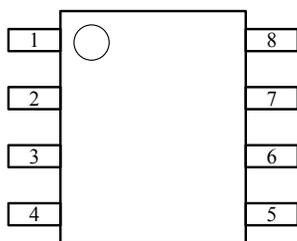
项目	记号	规格范围	单位	
漏极 - 源极电压	$V_{ds}$	20	V	
栅极 - 源极电压	$V_{gs}$	$\pm 12$	V	
漏极电流 ( $T_j=150^\circ C$ )	Id	$T_a=25^\circ C$	15	A
		$T_a=70^\circ C$	12	
漏极电流 (脉冲)	$I_{dm}$	50	A	
容许功耗	Pd	$T_c=25^\circ C$	5.0	W
		$T_c=70^\circ C$	3.2	
动作结合部温度	$T_j$	150	$^\circ C$	
保存温度范围	$T_{stg}$	$-55 \sim 150$	$^\circ C$	

## ■热特性

项目	记号	典型值	最大值	单位
最大结合部 - 环境热阻	$R_{\theta ja}$		120	$^\circ C/W$

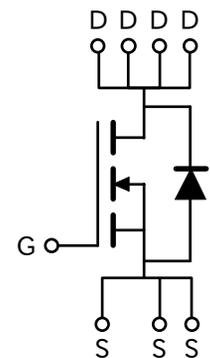
## ■引脚配置图

SOP-8(俯视图)



引脚编号	引脚名称
1	SOURCE
2	SOURCE
3	SOURCE
4	GATE
5	DRAIN
6	DRAIN
7	DRAIN
8	DRAIN

## ■电路图



# 单 N 沟道 MOSFET

ELM54116WSA-N

<http://www.elm-tech.com>

## ■电特性

如没有特别注明时,  $T_a=25^\circ\text{C}$

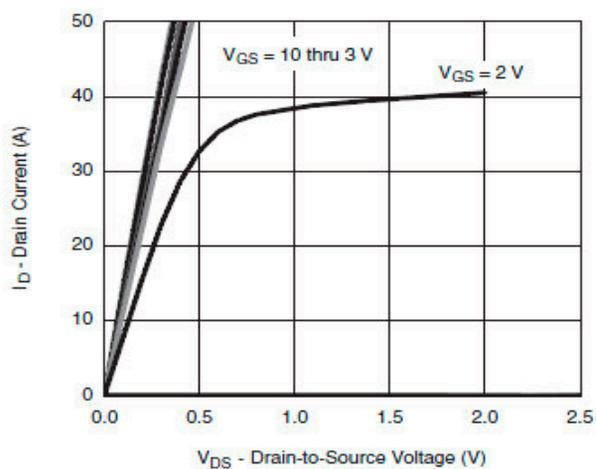
项目	记号	条件	最小值	典型值	最大值	单位
静态特性						
漏极 - 源极击穿电压	BV <sub>dss</sub>	$I_d=250\mu\text{A}, V_{gs}=0\text{V}$	20			V
栅极接地时漏极电流	I <sub>dss</sub>	$V_{ds}=16\text{V}, V_{gs}=0\text{V}$			1	$\mu\text{A}$
		$V_{ds}=16\text{V}, V_{gs}=0\text{V}, T_a=85^\circ\text{C}$			10	
栅极漏电电流	I <sub>gss</sub>	$V_{ds}=0\text{V}, V_{gs}=\pm 20\text{V}$			$\pm 100$	nA
栅极阈值电压	V <sub>gs(th)</sub>	$V_{ds}=V_{gs}, I_d=250\mu\text{A}$	0.5		1.0	V
导通时漏极电流	I <sub>d(on)</sub>	$V_{gs}=10\text{V}, V_{ds}\geq 5\text{V}$	30			A
漏极 - 源极导通电阻	R <sub>ds(on)</sub>	$V_{gs}=4.5\text{V}, I_d=15\text{A}$		7.2	8.5	m $\Omega$
		$V_{gs}=2.5\text{V}, I_d=12\text{A}$		8.5	11.0	
正向跨导	G <sub>fs</sub>	$V_{ds}=15\text{V}, I_d=10\text{A}$		68		S
二极管正向压降	V <sub>sd</sub>	$I_s=3.2\text{A}, V_{gs}=0\text{V}$		0.7	1.3	V
寄生二极管最大连续电流	I <sub>s</sub>				4.5	A
动态特性						
输入电容	C <sub>iss</sub>	$V_{gs}=0\text{V}, V_{ds}=15\text{V}, f=1\text{MHz}$		1900		pF
输出电容	C <sub>oss</sub>			325		pF
反馈电容	C <sub>rss</sub>			145		pF
开关特性						
总栅极电荷	Q <sub>g</sub>	$V_{gs}=4.5\text{V}, V_{ds}=15\text{V}, I_d=10\text{A}$		18.0	30.0	nC
栅极 - 源极电荷	Q <sub>gs</sub>			3.8		nC
栅极 - 漏极电荷	Q <sub>gd</sub>			3.5		nC
导通延迟时间	t <sub>d(on)</sub>	$V_{gs}=10\text{V}, V_{ds}=15\text{V}$ $R_L=1.5\Omega, I_d=10\text{A}$ $R_{gen}=1.0\Omega$		8	16	ns
导通上升时间	t <sub>r</sub>			10	20	ns
关闭延迟时间	t <sub>d(off)</sub>			30	60	ns
关闭下降时间	t <sub>f</sub>			9	18	ns

# 单 N 沟道 MOSFET

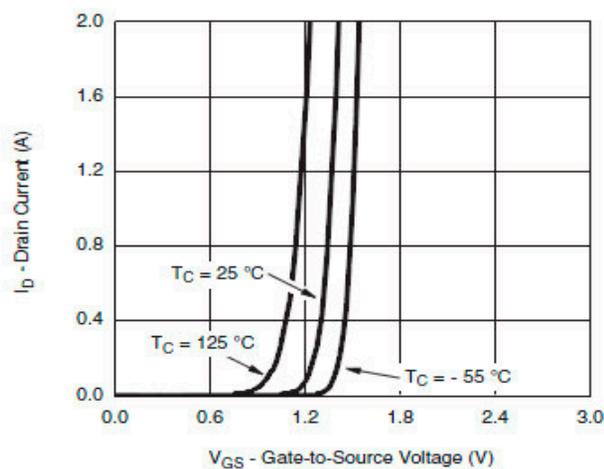
ELM54116WSA-N

<http://www.elm-tech.com>

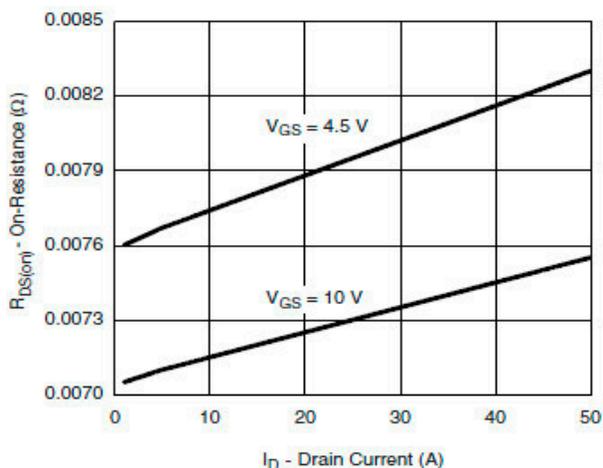
## 标准特性和热特性曲线



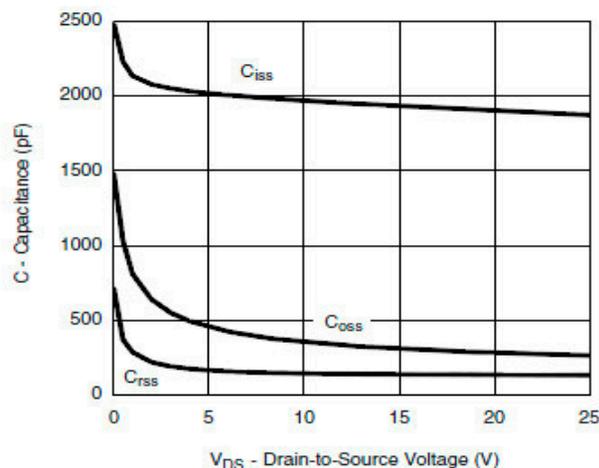
Output Characteristics



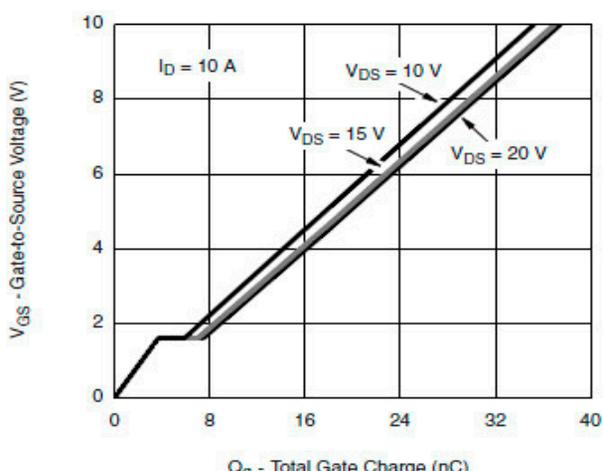
Transfer Characteristics



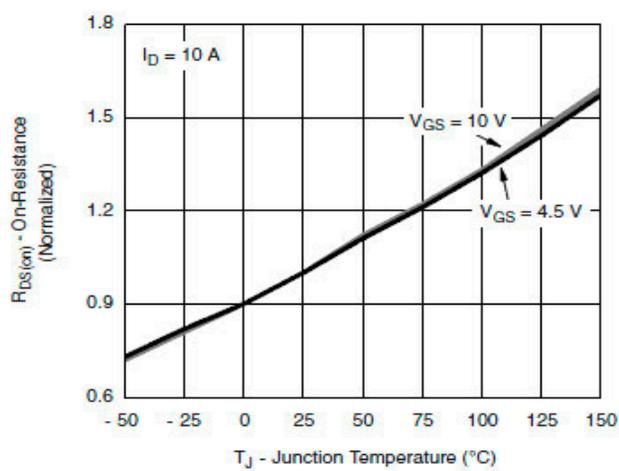
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



Gate Charge

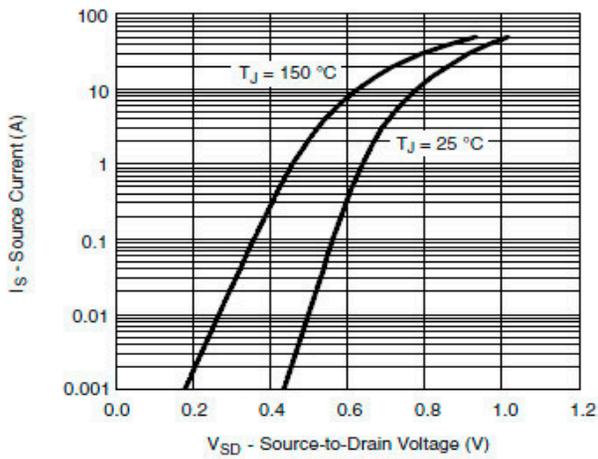


On-Resistance vs. Junction Temperature

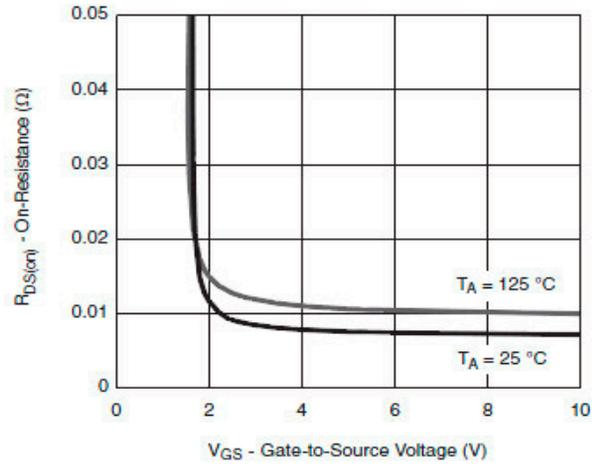
# 单 N 沟道 MOSFET

ELM54116WSA-N

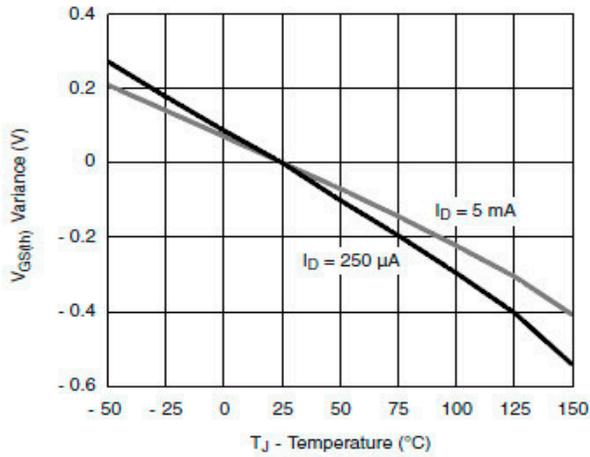
<http://www.elm-tech.com>



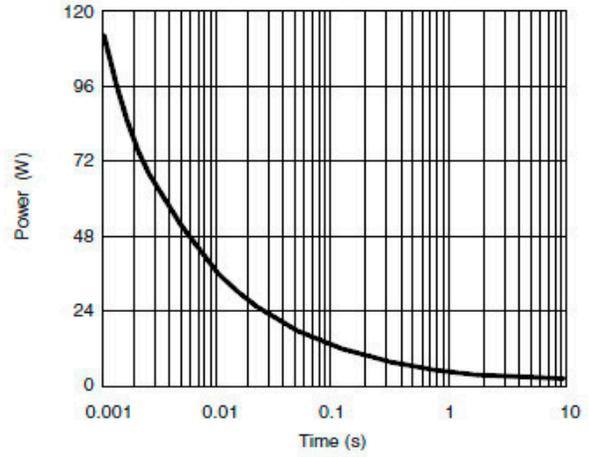
Source-Drain Diode Forward Voltage



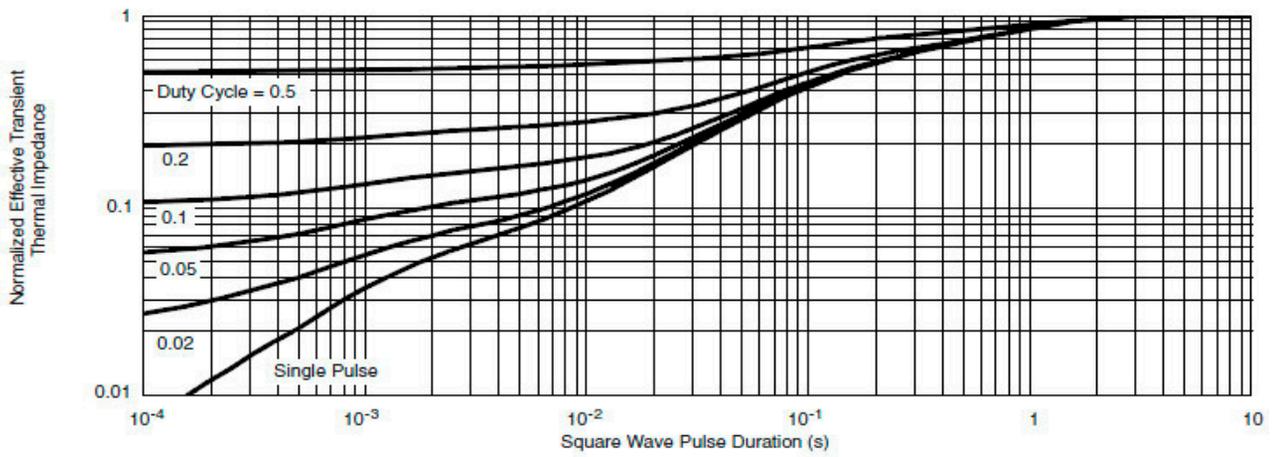
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

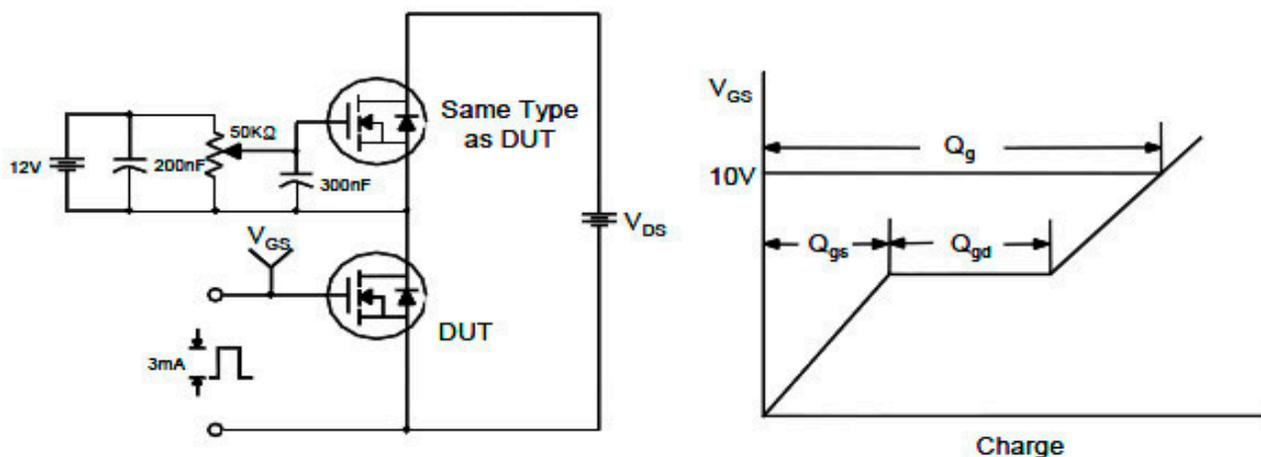
# 单 N 沟道 MOSFET

ELM54116WSA-N

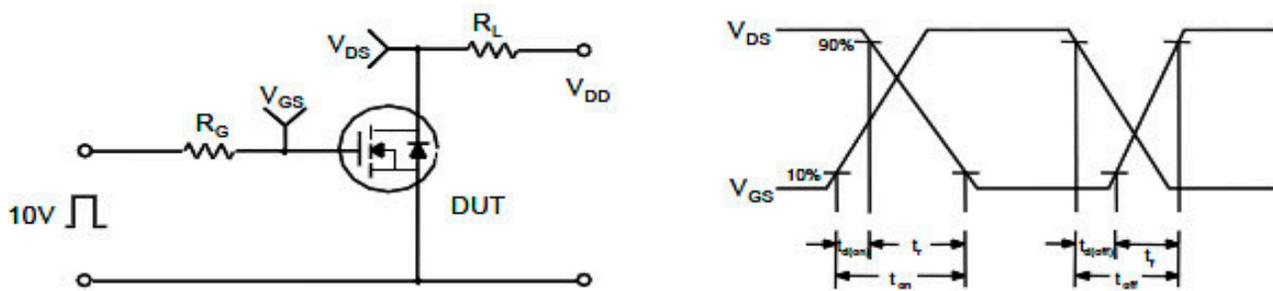
<http://www.elm-tech.com>

## 测试电路和波形

Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

